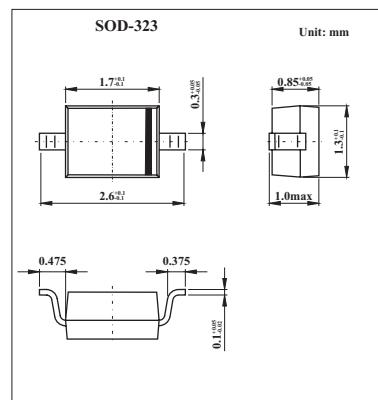


Silicon Epitaxial Planar Pin Diode**HVU131****■ Features**

- Low capacitance.(C=0.8pF max)
- Low forward resistance. ($r_f=1.0 \Omega$ max)

**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Value	Unit
Peak reverse voltage	V _{RM}	65	V
Reverse voltage	V _R	60	V
Forward current	I _F	100	mA
Power dissipation	P _d	150	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I _R	V _R = 60 V			0.1	µA
Reverse voltage	V _F	I _R = 10 mA			1.0	V
Capacitance	C	V _R = 1 V, f = 1 MHz			0.8	pF
Forward resistance	r _f	I _F = 10 mA, f = 100 MHz			1.0	Ω

■ Marking

Marking	P1
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